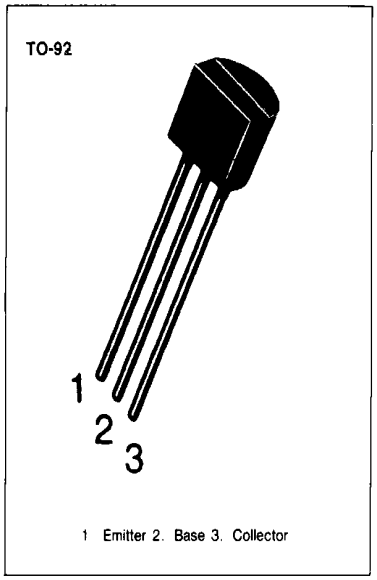
Transistors
USP2907A

USHA (INDIA) LTD

GENERAL PURPOSE TRANSISITOR

- **Collector-Emitter Voltage: V_{CEO}=60V**
- **Collector Dissipation: P_C (max)=625mW**



ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	−60	V
Collector-Emitter Voltage	V_{CEO}	−60	V
Emitter-Base Voltage	V_{EBO}	−5	V
Collector Current	I_C	−600	mA
Collector Dissipation	P_C	625	mW
Junction Temperature	T_j	150	°C
Storage Temperature	Tstg	−55~150	°C

• Refer to KSP2907 for graphs

ELECTRICAL CHARACTERISTICS (T_a=25°C)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=−10μA, I_E=0	−60			V
*Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=−10mA, I_B=0	−60			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=−10μA, I_C=0	−5			V
Collector Cut-off Current	I_{CBO}	V_{CB}=−50V, I_E=0			−10	nA
DC Current Gain	h_{FE}	I_C=−0.1mA, V_{CE}=−10V	75			
		I_C=−1mA, V_{CE}=−10V	100			
		I_C=−10mA, V_{CE}=−10V	100			
		*I_C=−150mA, V_{CE}=−10V	100		300	
		*I_C=−500mA, V_{CE}=−10V	50			
*Collector-Emitter Saturation Voltage	V_{CE}(sat)	I_C=−150mA, I_B=−15mA			−0.4	V
		I_C=−500mA, I_B=−50mA			−1.6	V
*Base-Emitter Saturation Voltage	V_{BE}(sat)	I_C=−150mA, I_B=−15mA			−1.3	V
		I_C=−500mA, I_B=−50mA			−2.6	V
Output Capacitance	C_{ob}	V_{CB}=−10V, I_E=0 f=1MHz			8	pF
*Current Gain Bandwidth Product	f_T	I_C=−50mA, V_{CE}=−20V f=100MHz	200			MHz
Turn On Time	t_{on}	V_{CC}=−30V, I_C=−150mA I_{B1}=−15mA			45	ns
Turn Off Time	toff	V_{CC}=−6V, I_C=−150mA I_{B1}=I_{B2}=−15mA			100	ns

*Pulse Test: Pulse Width=300μs, Duty Cycle=2%

Also available as a PN2907A

ISO 14001 CERTIFIED
AN ISO 9002 COMPANY